

L Number	Hits	Search Text	DB	Time stamp
241	0	recrystallized near polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/25 23:34
242	189	recrystallized near polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/25 23:34
243	55	recrystallized near polysilicon near layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/25 23:35
244	20	(recrystallized near polysilicon near layer) and (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/25 23:35
245	6	(recrystallized near polysilicon near layer) and (gate adj electrode) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/25 23:37
246	0	((recrystallized near polysilicon) near10 capacitor) and (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/25 23:36
247	0	((recrystallized near polysilicon) same capacitor) and (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/25 23:36
248	3	(recrystallized near polysilicon).clm. and (gate adj electrode) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/25 23:37
249	4	(recrystallized near polysilicon).clm. and (gate).clm. and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/25 23:37
250	1	(recrystallized near polysilicon).clm. and (gate).clm. and capacitor.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/25 23:40

251	1	(recrystallized adj polysilicon).ti,ab,clm. and (gate).clm. and capacitor.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/25 23:40
252	1	(recrystallized adj polysilicon).ti,ab,clm. and (gate).clm. and capacitor.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/25 23:40
253	2	(recrystallized adj polysilicon).ti,ab,clm. and (gate).ti,ab,clm. and capacitor.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/25 23:52
254	23	(recrystallized adj polysilicon) and (gate).ti,ab,clm. and capacitor.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/25 23:53
255	162	recrystallized adj polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/25 23:53
256	4	(recrystallized adj polysilicon) near10 (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/25 23:53